

Integrated circuit copper plateable barriers

ABSTRACT OF THE INVENTION

5 A trench (70) is formed in a dielectric layer (20). A first metal layer (80) is formed in the trench using physical vapor deposition. A second metal layer (100) is formed in the trench (70) over the first metal layer (80) using chemical vapor deposition. Copper (110) is used to
10 fill the trench (70) by electroplating copper directly onto the second metal (100).